Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2209	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 15:56
S2	30	(US-20020041028-$ or US-20020117737-$ or US-20030001278-$ or US-20030020168-$ or US-20030020169-$ or US-20030085473-$ or US-20030155657-$ or US-20030183939-$ or US-20030205825-$ or US-20030218256-$ or US-20040119164-$ or US-20040130030-$ or US-20040130035-$ or US-20040188850-$ or US-20050012223-$ or US-20050093108-$ or US-20050093168-$).did. or (US-5739579-$ or US-5990011-$ or US-6037664-$ or US-6083822-$ or US-6144099-$ or US-6359328-$ or US-6559546-$ or US-6686662-$ or US-6734116-$ or US-6794693-$ or US-6873057-$ or US-6879042-$ or US-6885105-$).did.	US-PGPUB; USPAT	OR	ON	2005/05/09 09:03
S3	996	(438/672).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:21
S4	1451	(438/687).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:40
S5	889	damascene and "etch stop".ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:41

S6	197	damascene and "etch stop".ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:47
S7	34	damascene and ("etch stop" with (composit or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:50
S8	121	damascene and ("etch stop" with (composite or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:28

| S9 | 72 | (US-20020041028-$ or US-20020117737-$ or US-20030001278-$ or US-20030020168-$ or US-20030020169-$ or US-20030085473-$ or US-20030155657-$ or US-20030183939-$ or US-20030205825-$ or US-20030218256-$ or US-20040119164-$ or US-20040130030-$ or US-20040130035-$ or US-20040188850-$ or US-20050012223-$ or US-20050093108-$ or US-20050093168-$ or US-20030207562-$ or US-20030113995-$ or US-20020039836-$ or US-20050006776-$ or US-20040166674-$ or US-20030042613-$ or US-20020019131-$ or US-20010054765-$ or US-20010004550-$).did. or (US-20050023694-$ or US-20040186223-$ or US-20040147100-$ or US-20030134521-$ or US-20030096090-$ or US-20030089992-$ or US-20010034121-$ or US-20040191977-$ or US-20020140103-$).did. or (US-5739579-$ or US-5990011-$ or US-6037664-$ or US-6083822-$ or US-6144099-$ or US-6359328-$ or US-6559546-$ or US-6686662-$ or US-6734116-$ or US-6794693-$ or US-6873057-$ or US-6879042-$ or US-6885105-$ or US-6830971-$ or US-6777323-$ or US-6683002-$ or US-6589863-$ or US-6495448-$ or US-6251770-$ or US-6153514-$ or US-5904565-$ or US-6562712-$ or US-6551872-$ or US-6440840-$ or US-6391713-$ or US-6365506-$). did. or (US-6331479-$ or US-5968333-$ or US-6831366-$ or US-6734110-$ or US-6455417-$ or US-6440838-$ or US-6753260-$ or US-6424021-$ or US-5935762-$ or US-6107188-$).did. or (US-6107188-$).did. | US-PGPUB; USPAT; DERWENT | OR | ON | 2005/05/09 09:58 |

S10	3	("6177364" | "6440838" | "6498399").PN. OR ("6734116"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S11	273	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S12	358	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:47
S13	2	("6734116").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 10:40
S14	61	damascene and ("etch stop" with (composite or multi-layer)) and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 12:26
S15	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 12:26
S16	130	S12 and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S17	182	("spin on glass" or SOG) and "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S18	32	("spin on glass" or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:23

S19	1	("spin on polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S20	1	("spin-on-polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S21	1	((spin adj on adj polymer) or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:25
S22	32	((spin adj on adj glass) or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:33
S23	8	"film hardness" and FSG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:36
S24	0	hardness with "spin of glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S25	0	hardness with "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S26	0	hardness same "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37

S27	17	hardness with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:49
S28	8	GPa with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:51
S29	0	hardness and spin adj on adj glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:07
S30	17	(etch$3 near2 selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:14
S31	2	(etch$3 near2 selectivity) with (SiCN and SiCO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:19
S32	7	(etch$3 near2 selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S33	0	("10365924").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:32
S34	0	"10365924".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:33

S35	17	(etch$3 adj selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:39
S36	0	("200400161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:41
S37	2	("0161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:40
S38	5	"414467".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:41
S39	114	S12 and selectivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:48
S40	8	(selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S41	50	damascene and ("etch stop" with (composite or multi-layer)) and "silicon carbide" and ("silicon dioxide" or "silicon oxide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:15
S42	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 10:57

| S43 | 2 | ("6873057").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/10 13:28 |
| S44 | 0 | ("s9and(OSGnear2"dielectriclayer")").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/10 13:29 |

S48	100	damascene and (dielectric or ILD) near2 ("organo-silicate glass" or osg)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 13:32
S49	265	damascene and "compressive stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:54
S50	118	damascene and "compressive stress" with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:58
S51	81	damascene and "compressive stress" with layer and "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:35
S52	2	damascene and "compressive stress" with "tensile stress" with etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:47
S53	0	("2005/0110153").URPN.	USPAT	OR	ON	2005/11/18 16:46
S54	17	damascene and "compressive stress" same "tensile stress" same etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:02
S55	9	damascene and "compressive stress" with (es or "etch stop")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:07
S56	4	"compressive stress" with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:05

S57	1196	(es or "etch stop") with dyne$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:30
S58	45	("etch stop") with dyne$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:31
S59	0	("etch stop") with dyne$3 with (SiCN or SiCO or SiN or SiO or SiC or SiO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:15

S61	4	damascene with dyne$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:32
S62	32	damascene and dyne$3 with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:37
S63	8	"film hardness" and "elastic modulus" and damascene	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:37